

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): A laminated resist for immersion lithography using ultraviolet light of a wavelength of not less than 193 nm for exposing, in which a photoresist layer (L1) and a protective layer (L2) are formed on a substrate, and the protective layer (L2) forms the outermost surface of the laminated resist and is characterized in that:

- (1) an absorption coefficient in ultraviolet light of a wavelength of not less than 193 nm is not more than $1.0 \mu\text{m}^{-1}$,
- (2) a dissolution rate in a developing solution is not less than 50 nm/sec, and
- (3) a dissolution rate in pure water is not more than 10 nm/min.

2. (original): The laminated resist for immersion lithography of Claim 1, wherein the dissolution rate of the protective layer (L2) in a developing solution is not less than 100 nm/sec.

3. (currently amended): The laminated resist for immersion lithography of Claim 1 or 2, wherein the dissolution rate of the protective layer (L2) in pure water is not more than 5 nm/min.

4. (currently amended): The laminated resist for immersion lithography of Claim ~~1any of Claims 1 to 3~~, wherein a contact angle of water of the protective layer (L2) is not less than 70°.

5. (currently amended): The laminated resist for immersion lithography of Claim ~~1any of Claims 1 to 3~~, wherein a contact angle of water of the protective layer (L2) is not less than 80°.

6. (currently amended): The laminated resist for immersion lithography of Claim ~~1any of Claims 1 to 5~~, wherein the protective layer (L2) is a layer comprising a fluorine-containing polymer (A1) having hydrophilic functional group Y.

7. (original): The laminated resist for immersion lithography of Claim 6, wherein the hydrophilic functional group Y is at least one selected from OH group, COOH group and SO₃H group.

8. (original): A laminated resist for immersion lithography using ultraviolet light of a wavelength of not less than 193 nm for exposing, in which a photoresist layer (L3) is formed on a substrate as an outermost surface of the laminated resist and is characterized by containing (A2) a fluorine-containing polymer having protective group Y² which can be converted to an alkali soluble group by dissociation with an acid and (B2) a photoacid generator.

9. (original): The laminated resist for immersion lithography of Claim 8, wherein a contact angle of water of the photoresist layer (L3) is not less than 70°.

10. (original): The laminated resist for immersion lithography of Claim 8, wherein a contact angle of water of the photoresist layer (L3) is not less than 80°.

11. (new): The laminated resist for immersion lithography of Claim 2, wherein a contact angle of water of the protective layer (L2) is not less than 70°.

12. (new): The laminated resist for immersion lithography of Claim 3, wherein a contact angle of water of the protective layer (L2) is not less than 70°.

13. (new): The laminated resist for immersion lithography of Claim 2, wherein a contact angle of water of the protective layer (L2) is not less than 80°.

14. (new): The laminated resist for immersion lithography of Claim 3, wherein a contact angle of water of the protective layer (L2) is not less than 80°.

15. (new): The laminated resist for immersion lithography of Claim 2, wherein the protective layer (L2) is a layer comprising a fluorine-containing polymer (A1) having hydrophilic functional group Y.

16. (new): The laminated resist for immersion lithography of Claim 3, wherein the protective layer (L2) is a layer comprising a fluorine-containing polymer (A1) having hydrophilic functional group Y.

17. (new): The laminated resist for immersion lithography of Claim 15, wherein the hydrophilic functional group Y is at least one selected from OH group, COOH group and SO₃H group.

18. (new): The laminated resist for immersion lithography of Claim 16, wherein the hydrophilic functional group Y is at least one selected from OH group, COOH group and SO₃H group.